	Type	Hits	S arch Text	DBs
1	BRS	2282079	wafer or substrate or die or chip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	190239	(second or another or addition$4) near4 (wafer or substrate or die or chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	90883	(separat$4 or cleav$4) near4 (wafer or substrate or die or chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	9939	(bond$4 or join$4) near4 ((second or another or addition$4) near4 (wafer or substrate or die or chip))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	2724	((bond$4 or join$4) near4 ((second or another or addition$4) near4 (wafer or substrate or die or chip))) and ((separat$4 or cleav$4) near4 (wafer or substrate or die or chip))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	599	((bond$4 or join$4) near4 ((second or another or addition$4) near4 (wafer or substrate or die or chip))) same ((separat$4 or cleav$4) near4 (wafer or substrate or die or chip))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	BRS	321	(semiconductor or silicon) and (@ay < "1999") and (((bond$4 or join$4) near4 ((second or another or addition$4) near4 (wafer or substrate or die or chip))) same ((separat$4 or cleav$4) near4 (wafer or substrate or die or chip)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS	90997	(separat$4 or cleav$4) near4 (wafer or substrate or die or chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
9	BRS	91022	(separat$4 or cleav$4 or smart-cut$4 or smart adj cut$4) near4 (wafer or substrate or die or chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	BRS	414726	mask$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11	BRS	4465	((separat$4 or cleav$4 or smart-cut$4 or smart adj cut$4) near4 (wafer or substrate or die or chip)) same mask$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
12	BRS	1549	((separat$4 or cleav$4 or smart-cut$4 or smart adj cut$4) near4 (wafer or substrate or die or chip)) near8 mask$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
13	BRS	14032	(separat$4 or cleav$4 or smart-cut$4 or smart adj cut$4) near4 (porous$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	BRS	635	(separat$4 or cleav$4 or smart-cut$4 or smart adj cut$4) near4 (porous$4) near4 (wafer or substrate or chip or die)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
15	BRS	824	mask$4 near4 porous$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	BRS	10	((separat$4 or cleav$4 or smart-cut$4 or smart adj cut$4) near4 (porous$4) near4 (wafer or substrate or chip or die)) and (mask$4 near4 porous$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
17	BRS	43	((separat$4 or cleav$4 or smart-cut$4 or smart adj cut$4) near4 (porous$4)) and (mask$4 near4 porous$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Typ	Hits	Search Text	DBs
18	BRS	33	(((separat$4 or cleav$4 or smart-cut$4 or smart adj cut$4 (porous$4)) and (mask$4 near4 porous$4)) not (((separat$4 or cleav$4 or smart-cut$4 or smart adj cut$4) near4 (porous$4) near4 (wafer or substrate or chip or die)) and (mask$4 near4 porous$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
19	IS&R	847	((438/960) or (438/455) or (438/459)).CCLS.	USPAT; US-PGPUB
20	BRS	581	(((438/960) or (438/455) or (438/459)).CCLS.) and (@ay < "1999"	USPAT
21	BRS	185	(((separat$4 or cleav$4 or smart-cut$4 or smart adj cut$4) near4 porous$4) and mask$4 and (semiconductor or silicion or si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
22	BRS	103	(((separat$4 or cleav$4 or smart-cut$4 or smart adj cut$4) near4 porous$4) and mask$4 and (wafer or substratei)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
23	BRS	16	(((separat$4 or cleav$4 or smart-cut$4 or smart adj cut$4) near4 porous$4) and mask$4 and (wafer or substratei)) not (((separat$4 or cleav$4 or smart-cut$4 or smart adj cut$4) near4 porous$4) and mask$4 and (semiconductor or silicion or si))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
24	BRS	41	((separat$4 or cleav$4) near4 porous$4) and (semiconductor or silicion or si) and (smart-cut$4 or smart adj cut$4 or (("h.sub.2" or hydrogen) near4 (inplant$4 or implant$4)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
25	BRS	55	((separat$4 or cleav$4) same porous$4) and (semiconductor or silicion or si) and (smart-cut$4 or smart adj cut$4 or (("h.sub.2" or hydrogen) near4 (inplant$4 or implant$4)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	S arch Text	DBs
26	BRS	14	(((separat$4 or cleav$4) same porous$4) and (semiconductor or silicion or si) and (smart-cut$4 or smart adj cut$4 or (("h.sub.2" or hydrogen) near4 (inplant$4 or implant$4)))) not ((((separat$4 or cleav$4) near4 porous$4) and (semiconductor or silicion or si) and (smart-cut$4 or smart adj cut$4 or (("h.sub.2" or hydrogen) near4 (inplant$4 or implant$4))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
27	BRS	21	((((separat$4 or cleav$4) same porous$4) and (semiconductor or silicion or si) and (smart-cut$4 or smart adj cut$4 or (("h.sub.2" or hydrogen) near4 (inplant$4 or implant$4))))) not ((((separat$4 or cleav$4) near4 porous$4) and (semiconductor or silicion or si) and (smart-cut$4 or smart adj cut$4 or (("h.sub.2" or hydrogen) near4 (inplant$4 or implant$4))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
28	BRS	8	((((separat$4 or cleav$4) same porous$4) and (semiconductor or silicion or si) and (smart-cut$4 or smart adj cut$4 or (("h.sub.2" or hydrogen) near4 (inplant$4 or implant$4))))) not ((((separat$4 or cleav$4) near4 porous$4) and (semiconductor or silicion or si) and (smart-cut$4 or smart adj cut$4 or (("h.sub.2" or hydrogen) near4 (inplant$4 or implant$4))))) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
29	BRS	86	(((separat$4 or cleav$4) same porous$4) and (semiconductor or silicion or si) and (smart-cut$4 or smart adj cut$4 or (("h.sub.2" or hydrogen) near4 (inplant$4 or implant$4))))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
30	BRS	30	(((separat$4 or cleav$4) same porous$4) and (semiconductor or silicion or si) and (smart-cut$4 or smart adj cut$4 or ("h.sub.2" or hydrogen) near4 (inplant$4 or implant$4))) and (@ay < "2000")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
31	IS&R	2	(("6602761") or ("6271101")).PN.	USPAT
32	IS&R	11	((("6,020,252") or ("5,985,681") or ("5,882,987") or ("5,374,564") or ("5,714,395") or ("6,331,208") or ("5,371,037") or ("6,171,982") or ("6,342,433") or ("6,294,478") or ("6,271,101")).PN.	USPAT

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